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RESPONSE UNDER 37 C.F.R. § 1.116
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| To: Commissioner for Patents | Total Pages Sent: | 7 |
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| Facsimile Number: (571) 273-8300 | Transmission Date: | September 7, 2006 |

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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|-------------|---|-------------|-------------------------------------|
| Applicant: | Haupt | Docket No.: | INTECH 3.0-104 (2003 P 51718 US) |
| Serial No: | 10/766,053 | Art Unit: | 2822 |
| Date Filed: | January 28, 2004 | Examiner: | Thanh Y. Tran |
| Title: | Method for N+ Doping of Amorphous Silicon and Polysilicon Electrodes in Deep Trenches | | |

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- Certification of Facsimile Transmission (1 page)
- Response Under 37 C.F.R. § 1.116 (6 pages)

Respectfully submitted,

Theresa L. O'Connor
Legal Assistant

Confirmation Respectfully Requested

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For: Method for N+ Doping of Amorphous Silicon and Polysilicon Electrodes
in Deep Trenches

Mail Stop: After Final
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

RESPONSE UNDER 37 CFR § 1.116

Dear Sir:

Applicant respectfully submits the following remarks in response to Examiner's Office Action dated July 14, 2006, which Action was made final. Applicant respectfully requests that these remarks be entered in pursuant to the provisions of 37 CFR § 1.116 in order to place the claims in a condition for allowance or to place the claims in a better condition for appeal, and respectfully requests reconsideration of claims 1-27.

INTECH 3.0-104
(2003 P 51718 US)

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